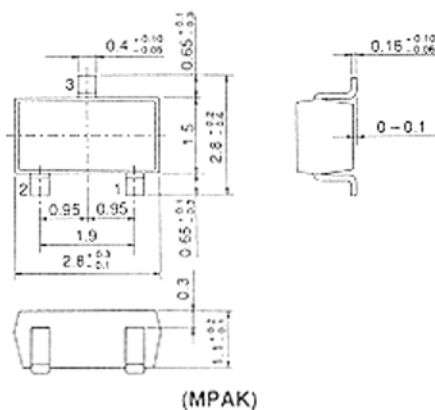


2SK1070

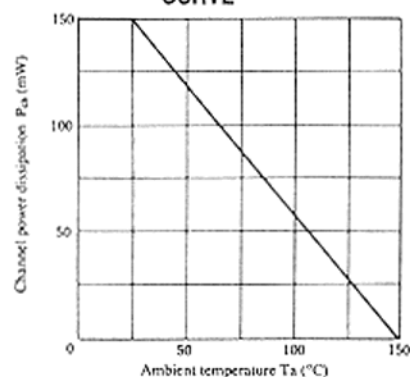
SILICON N-CHANNEL JUNCTION FET
LOW FREQUENCY/HIGH FREQUENCY
AMPLIFIER



■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SK1070	Unit
Gate to drain voltage	V_{GDO}	-22	V
Gate to source voltage	V_{GSO}	-22	V
Drain current	I_D	50	mA
Gate current	I_G	10	mA
Channel power dissipation	P_{ch}	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

MAXIMUM CHANNEL DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Gate cutoff current	I_{GSS}	$V_{GS} = -15V, V_{DS} = 0$	—	—	-10	nA
Gate to source breakdown voltage	$V_{(BR)GSS}$	$I_G = -10\mu A, V_{DS} = 0$	-22	—	—	V
Drain current	I_{DSS}^*	$V_{DS} = 5V, V_{GS} = 0, \text{Pulse Test}$	6	—	40	mA
Gate to source cutoff voltage	$V_{GS(off)}$	$V_{DS} = 5V, I_D = 10\mu A$	0	—	-2.5	V
Forward transfer admittance	$ y_{fs} $	$V_{DS} = 5V, V_{GS} = 0, f = 1kHz$	20	30	—	mS
Input capacitance	C_{iss}	$V_{DS} = 5V, V_{GS} = 0, f = 1MHz$	—	9	—	pF

* The 2SK1070 is grouped by I_{DSS} as follows.

Grade	B	C	D	E
Mark	PIB	PIC	PID	PIE
I_{DSS}	6 to 14	12 to 22	18 to 30	27 to 40

■ See characteristic curves of 2SK435.